

Specification Sheet

GaN Wafer

(Gallium Nitride, Si-Doped, N type, Purity: >99.9%, Diameter: 2")

Stock No: NS6130-10-1263, CAS: 25617-97-4

Product	:	GaN Wafer
Stock No	:	NS6130-10-1263
CAS	:	25617-97-4
Purity	:	>99.9%
Diameter	:	2"
Thickness	:	4 μ m \pm 1 μ m
Thickness of Sapphire	:	650 \pm 25 μ m for 4inch
Substrate	:	Sapphire
Dopant	:	Silicon
Type	:	N Type
TTV	:	\leq 10 μ m
Warp	:	\leq 10 μ m
Epi-Layer	:	Doped GaN Epitaxialon Sapphire
Orientation	:	C-axis (001) \pm 1.0o
Resistivity	:	0.01 - 0.1 Ohm-cm
Bow	:	\leq 10 μ m
Edge Profile	:	Rounded
Front Side Surface	:	Polished
Backside Side Surface	:	Etched
Main Inspect Verifier	:	Manager QC

Note: Product Specification are subject to amendment and may change over time